

**CLEAN VERSION OF PARTIAL SPECIFICATION**  
**AND ALL PENDING CLAIMS**

**In The Specification:**

Please replace the paragraphs located on page 12, lines 18-27, as follows:

“Another embodiment of the invention may use a combined resist strip and barrier etch step to reduced etching damage as described in U.S. Patent No. 6,518,174 entitled “A Combined Resist Strip And Barrier Etch Process For Dual Damascene Structures” by Rao Annapragada and Reza Sadjadi, with the same filing date, and which is incorporated by reference.

A1 Sidewalls formed by the crust may be removed during the stripping of the resist or may be removed using a separate wet stripping as described in U.S. Patent No. 6,413,877 entitled “Method of Preventing Damage To Organo-Silicate-Glass Materials During Resist Stripping” by Rao Anapragada, with the same filing date, and which is incorporated by reference.”

**In The Abstract:**

Please replace the abstract located on page 17 as follows:

**ABSTRACT**

A2 “A device for etching stacks on a substrate is provided. The device comprises: a plasma chamber with chamber walls; a plasma confinement device for reducing plasma contact with the chamber walls; a gas source; plasma generation and energizing device; and an exhaust system for pumping plasma away. The gas source comprises a fluorine containing gas source and an ammonia containing gas source.”

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